OPB825, OPB825A

Obsolete (OPB825B, OPB825R)

Features:

- Non-contact switching
- Fast switching speed
- 0.160" (4.06 mm) wide slot
- 0.300" (7.62 mm) lead spacing





Description:

Each OPB825 and OPB825A have an infrared LED. All devices have a NPN silicon phototransistor mounted in a low-cost black plastic housing on opposite sides of a 0.160" (4.064 mm) wide slot.

OPB825 have no mounting tabs and is intended for direct insertion into PCBoards or dual-in-line sockets. OPB825A has one mounting tab on the phototransistor side.

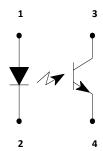
Phototransistor switching takes place whenever an opaque object passes through the slot.

Applications:

- Non-contact interruptive object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety
- Ticket Sensing

| Ordering Information | | | |
|-------------------------|----------------------------------|--|--|
| Part Number Description | | | |
| OPB825 | Slotted Switch (no tabs) IR-LED | | |
| OPB825A | Slotted Switch (one tab) IR-LED | | |
| OPB825B Obsolete | Slotted Switch (two tabs) IR-LED | | |
| OPB825R Obsolete | Slotted Switch (no tabs) Red-LED | | |

| Pin # | Description | Pin # | Description |
|-------|-------------|-------|-------------|
| 1 | Anode | 3 | Collector |
| 2 | Cathode | 4 | Emitter |





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OPB825, OPB825A

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Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

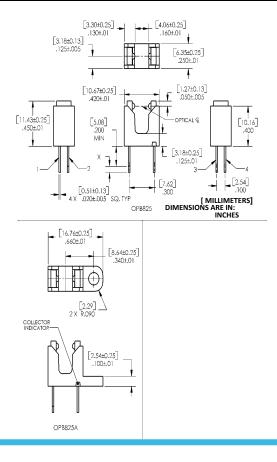
| Storage & Operating Temperature Range | -40° C to +85° C |
|--|------------------|
| Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 sec. with soldering iron] (1) | 260° C |

| Input Diode | OPB825—A |
|-------------|----------|
| | |

| Forward DC Current | 50 mA |
|--|--------|
| Peak Forward Current (1 μs pulse width, 300 pps) | 3 A |
| Reverse DC Voltage | 2 V |
| Power Dissipation ⁽²⁾ | 100 mW |

Output Phototransistor OPB825—A

| Collector-Emitter Voltage | 30 V |
|----------------------------------|--------|
| Emitter-Collector Voltage | 5 V |
| Collector DC Current | 30 mA |
| Power Dissipation ⁽²⁾ | 100 mW |



OPB825, OPB825A

Obsolete (OPB825B, OPB825R)



Electrical Specifications

OPB825, OPB825A

Electrical Characteristics (T_A = 25° C unless otherwise noted)

| SYMBOL | PARAMETER | MIN | TYP | MAX | UNITS | TEST CONDITIONS |
|----------------------|---|-----|-----|-----|-------|---|
| Input Diode | nput Diode (See OP240 for additional information) | | | | | |
| V _F | Forward Voltage | - | - | 1.6 | ٧ | I _F = 20 mA |
| I _R | Reverse Current | - | 1 | 100 | μΑ | V _R = 2 V |
| Output Pho | Output Phototransistor (See OP550 for additional information) | | | | | |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | 30 | 1 | 1 | ٧ | I _C = 1 mA |
| V _{(BR)ECO} | Emitter-Collector Breakdown Voltage | 5 | 1 | 1 | ٧ | Ι _Ε = 100 μΑ |
| I _{CEO} | Collector Dark Current | - | ı | 100 | nA | $V_{CE} = 10 \text{ V}, I_F = 0, E_E = 0$ |
| Combined | Combined | | | | | |
| V _{CE(SAT)} | Collector-Emitter Saturation | - | - | 0.4 | V | I _C = 250 μA, I _F = 20 mA |
| I _{C(ON)} | On-State Collector Current | 1.0 | - | - | mA | I _F = 20 mA, V _{CE} = 10 V |

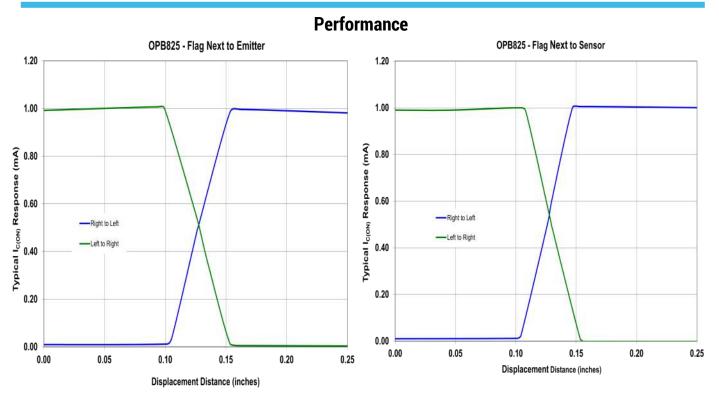
Notes:

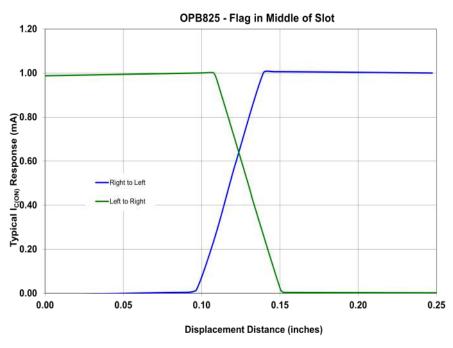
- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.67 mW/°C above 25° C.
- (3) All parameters tested using pulse techniques.
- (4) Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones.
- (5) Simulates optical path blocked with thick paper.

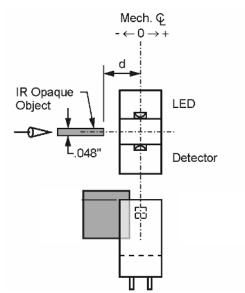
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Test Schematic